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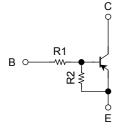
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process) (Bias Resistor built-in Transistor)

## RN2101FT,RN2102FT,RN2103FT RN2104FT,RN2105FT,RN2106FT

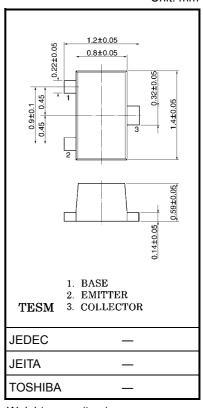
Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications.

- High-density mount is possible because of devices housed in very thin TESM packages.
- Incorporating a bias resistor into a transistor reduces parts count. Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.
- Wide range of resistor values are available to use in various circuit designs.
- Complementary to RN1101FT~1106FT

## **Equivalent Circuit and Bias Resistor Values**



Type No.	R1 (kΩ)	R2 (kΩ)
RN2101FT	4.7	4.7
RN2102FT	10	10
RN2103FT	22	22
RN2104FT	47	47
RN2105FT	2.2	47
RN2106FT	4.7	47



Weight: g (typ.)

## Maximum Ratings (Ta = 25°C)

Charact	Symbol	Rating	Unit		
Collector-base voltage	RN2101FT~2106FT	V <sub>CBO</sub>	-50	V	
Collector-emitter voltage		V <sub>CEO</sub>	-50	V	
Emitter-base voltage	RN2101FT~2104FT	V <sub>EBO</sub>	-10	V	
Emilier-base voltage	RN2105FT, RN2106FT	▲EBO	-5		
Collector current		Ι <sub>C</sub>	-100	mA	
Collector power dissipation	RN2101FT~2106FT	P <sub>C</sub> (Note)	100	mW	
Junction temperature	RN2101F1~2100F1	Тj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

Note: Total rating

Unit: mm

Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	RN2101FT~2106FT	I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, \text{ I}_{E} = 0$	_		-100	nA
		ICEO	$V_{CE}=-50~V,~I_B=0$			-500	ΠA
	RN2101FT	Іево	$V_{EB} = -10 \text{ V}, \text{ I}_{C} = 0$	-0.82		-1.52	mA
	RN2102FT			-0.38		-0.71	
	RN2103FT			-0.17		-0.33	
Emitter cut-off current	RN2104FT			-0.082		-0.15	
	RN2105FT		$V_{EB} = -5 \text{ V}, \text{ I}_{C} = 0$	-0.078		-0.145	
	RN2106FT			-0.074		-0.138	
	RN2101FT		$V_{CE} = -5 V,$ $I_{C} = -10 mA$	30	_	_	
	RN2102FT			50	_	_	
DC autrent agin	RN2103FT			70			
DC current gain	RN2104FT	h <sub>FE</sub>		80		_	
	RN2105FT	-		80	_	_	
	RN2106FT			80	_	_	
Collector-emitter saturation voltage	RN2101FT~2106FT	V <sub>CE (sat)</sub>	$I_{C} = -5 \text{ mA},$ $I_{B} = -0.25 \text{ mA}$	_	-0.1	-0.3	V
	RN2101FT		$V_{CE} = -0.2 \text{ V},$ $I_{C} = -5 \text{ mA}$	-1.1		-2.0	V
	RN2102FT			-1.2		-2.4	
lanut valtana (ONI)	RN2103FT	- Vi (on)		-1.3		-3.0	
Input voltage (ON)	RN2104FT			-1.5		-5.0	
	RN2105FT			-0.6		-1.1	
	RN2106FT			-0.7		-1.3	
Input voltage (OFF)	RN2101FT~2104FT		$V_{CE} = -5 \text{ V},$ I <sub>C</sub> = -0.1 mA	-1.0		-1.5	· V
Input voltage (OFF)	RN2105FT, 2106FT	VI (OFF)		-0.5		-0.8	
Transition frequency	RN2101FT~2106FT	fT	$V_{CE} = -10 \text{ V},$ $I_{C} = -5 \text{ mA}$		200	_	MHz
Collector output capacitance	RN2101FT~2106FT	C <sub>ob</sub>	$\label{eq:VCB} \begin{array}{l} V_{CB} = -10 \ V, \ I_E = 0, \\ f = 1 \ MHz \end{array}$	_	3	6	pF
	RN2101FT			3.29	4.7	6.11	
	RN2102FT	- R1		7	10	13	kΩ
	RN2103FT			15.4	22	28.6	
Input resistor	RN2104FT			32.9	47	61.1	
	RN2105FT			1.54	2.2	2.86	
	RN2106FT			3.29	4.7	6.11	
	RN2101FT~2104FT	1	_	0.9	1.0	1.1	
Resistor ratio	RN2105FT	R1/R2		0.0421	0.0468	0.0515	
	RN2106FT			0.09	0.1	0.11	

Type Name	Marking
RN2101FT	Type name YA
RN2102FT	Type name YB
RN2103FT	Type name YC
RN2104FT	Type name YD
RN2105FT	Type name YE
RN2106FT	Type name

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